



R52K SERIES
1800-1200 VOLTS RANGE
2680 AMP AVG HOCKEY PUK
DIFFUSED JUNCTION RECTIFIER DIODES

VOLTAGE RATINGS

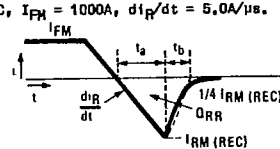
PART NUMBER	$V_{RRM}, V_R - (V)$ Max. rep. peak reverse and direct voltage		$V_{RSM} - (V)$ Max. non-rep. peak reverse voltage
	$T_J = 0^\circ \text{ to } 200^\circ\text{C}$	$T_J = -40^\circ \text{ to } 0^\circ\text{C}$	$T_J = 25^\circ \text{ to } 200^\circ\text{C}$
R52K18A	1800	1710	1800
R52K16A	1600	1520	1700
R52K14B	1400	1330	1500
R52K12B	1200	1200	1300

MAXIMUM ALLOWABLE RATINGS

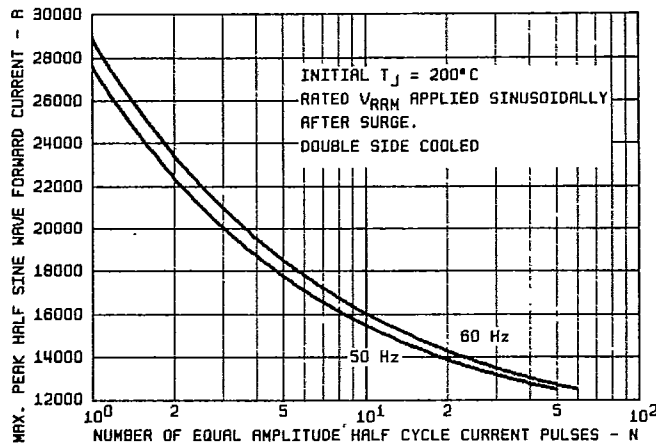
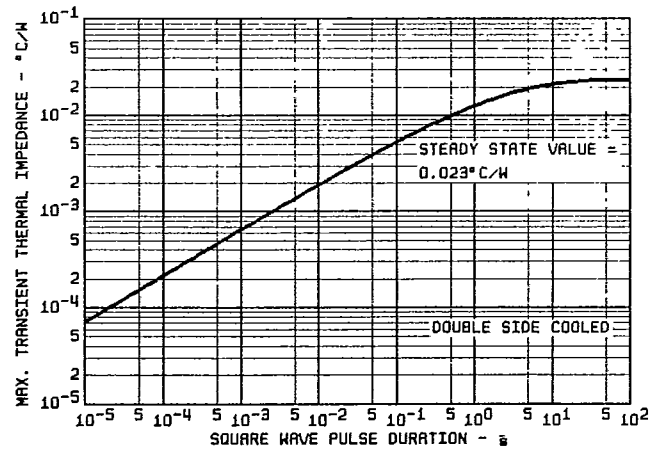
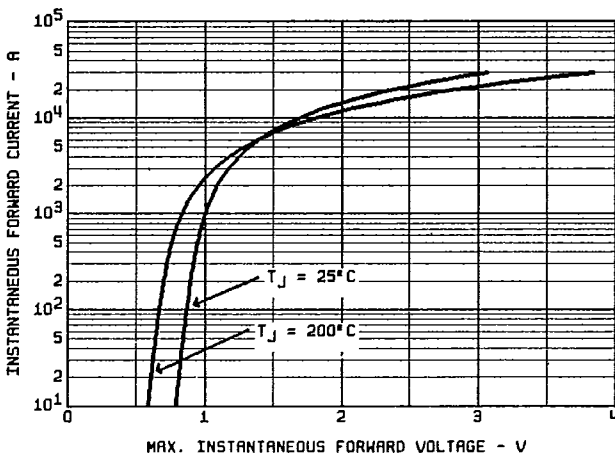
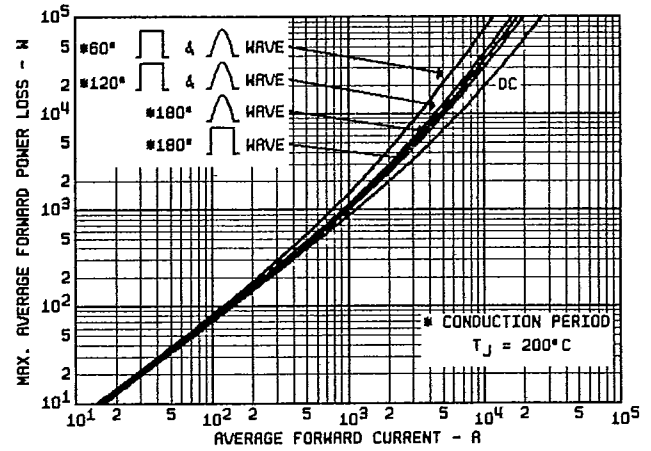
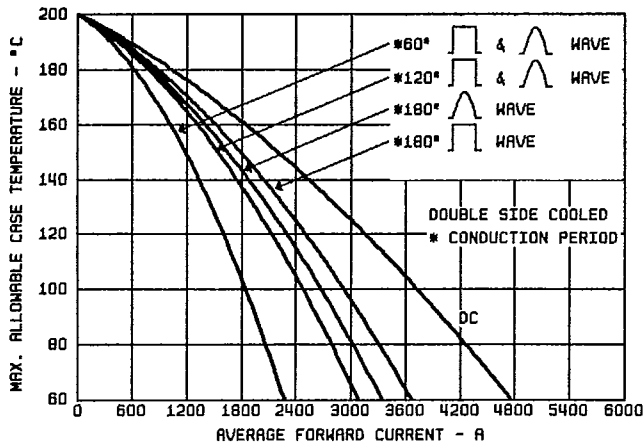
PARAMETER	VALUE	UNITS	NOTES
T_J Junction temperature	-40 to 200	$^\circ\text{C}$	
T_{stg} Storage temperature	-40 to 200	$^\circ\text{C}$	
$I_{F(AV)}$ Max. av. current	2680	A	180 $^\circ$ half sine wave
ϕ Max. T_C	100	$^\circ\text{C}$	
$I_{F(RMS)}$ Nom. RMS current	4210	A	
I_{FSM} Max. peak non-rep. surge current	27600	A	50Hz half cycle sine wave Initial $T_J = 200^\circ\text{C}$, rated V_{RRM} applied after surge.
	28900		60Hz half cycle sine wave
	32800		50Hz half cycle sine wave Initial $T_J = 200^\circ\text{C}$, no voltage applied after surge.
	34400		60Hz half cycle sine wave
I^2t Max. I^2t capability	3810	kA^2s	$t = 10\text{ms}$ Initial $T_J = 200^\circ\text{C}$, rated V_{RRM} applied after surge.
	3480		$t = 8.3\text{ms}$
	5390		$t = 10\text{ms}$ Initial $T_J = 200^\circ\text{C}$, no voltage applied after surge.
	4920		$t = 8.3\text{ms}$
$I^2\sqrt{t}$ Max. $I^2\sqrt{t}$ capability	53900	kA^2/s	Initial $T_J = 200^\circ\text{C}$, no voltage applied after surge. I^2t for time $t_x = I^2\sqrt{t} \cdot \sqrt{t_x}$, $0.1 \leq t_x \leq 10\text{ms}$.
F Mounting force	22250(5000) \pm 10%	N(lbf)	

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CHARACTERISTICS

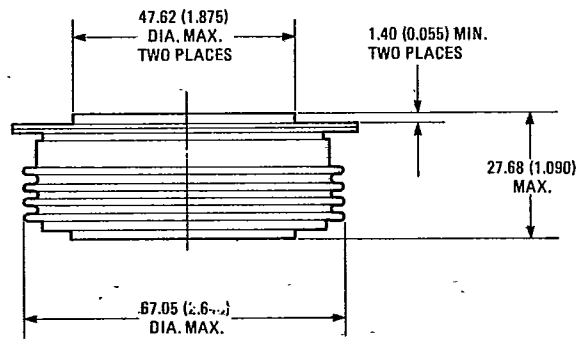
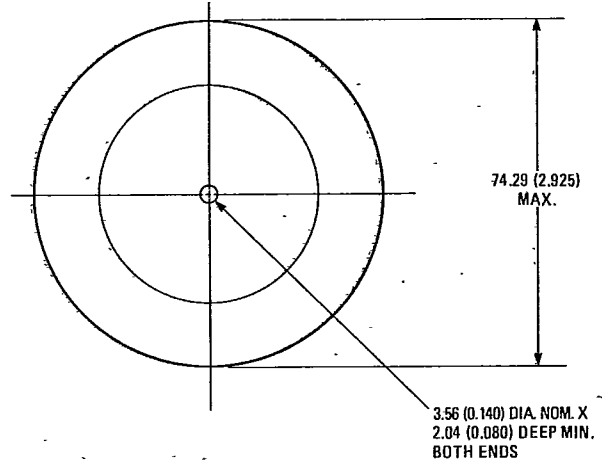
PARAMETER	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
V_{FM} Peak forward voltage	---	1.45	1.57	V	Initial $T_J = 25^\circ\text{C}$, 50-60Hz half sine, $I_{peak} = 8420\text{A}$.
$V_{F(TO)1}$ Low-level threshold	---	---	0.742	V	$T_J = 200^\circ\text{C}$ Av. power = $V_{F(TO)} \cdot I_{F(AV)} + r_F \cdot [I_{F(RMS)}]^2$ Use low level values for $I_{FM} \leq 2 I_{F(AV)}$
$V_{F(TO)2}$ High-level threshold	---	---	0.813		
r_{F1} Low-level resistance	---	---	0.112	m Ω	
r_{F2} High-level resistance	---	---	0.105		
t_a Reverse current rise	---	24.0	---	μs	$T_J = 175^\circ\text{C}$, $I_{FM} = 1000\text{A}$, $di_F/dt = 5.0\text{A}/\mu\text{s}$. 
t_b Reverse current fall	---	6.0	---	μs	
$I_{RM(REC)}$ Reverse current	---	120	---	A	
Q_{RR} Recovered charge	---	1800	---	μC	
I_{RM} Peak reverse current	---	40	100	mA	$T_J = 175^\circ\text{C}$. Max. rated V_{RRM} .
R_{thJC} Thermal resistance, junction-to-case	---	---	0.023	$^\circ\text{C}/\text{W}$	DC operation, double side
	---	---	0.025	$^\circ\text{C}/\text{W}$	180 $^\circ$ sine wave, double side
	---	---	0.025	$^\circ\text{C}/\text{W}$	120 $^\circ$ rectangular wave, double side
R_{thCS} Thermal resistance, case-to-sink	---	---	0.020	$^\circ\text{C}/\text{W}$	Mtg. surface smooth, flat and greased. Single side. For double side, divide value by 2.
wt Weight	---	425(15)	---	g(oz.)	
Case Style	00-200AC		JEDEC		

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CREEPAGE DISTANCE: 32.26 (1.270) MIN.
STRIKE DISTANCE: 23.78 (0.936) MIN.

Conforms to JEDEC Outline DO-200AC
All Dimensions in Millimeters and (Inches)